

**IN THE CLAIMS:**

This listing of claims will replace all prior versions, and listings of claims in the application.

Claims 1-8 (canceled)

1 9. (new) A photoresist laminate comprising:  
2 a substrate;  
3 a photoresist pattern with a reinforcing section formed by using an exposure and a  
4 developing solution,  
5 a sublayer film provided between the substrate and the photoresist pattern, the sublayer  
6 film being soluble in a developing solution used to form the photoresist pattern; and  
7 wherein there is provided in said photoresist pattern line section and a reinforcing section  
8 that continues to said line section and that has a greater width than a line width of said line  
9 section..

1 10. (new) A method of forming a photoresist laminate according to claim 9, comprising:  
2 forming on a substrate a sublayer film that is soluble in a developing solution used in a  
3 developing process;  
4 forming on the sublayer film a photoresist film;  
5 exposing the photoresist film; and  
6 developing the photoresist film by the developing solution.

1 11. (new) A method of evaluating a photoresist pattern, comprising:  
2 forming on a substrate a photoresist pattern with a reinforcing section, wherein there is  
3 provided a line section and a reinforcing section that continues to said line section and that has a  
4 greater width than a line width of said line section;  
5 providing on the substrate a sublayer film that is soluble in a developing solution used in  
6 a developing process;  
7 forming on the sublayer film a photoresist film;  
8 exposing the photoresist film; and  
9 developing the photoresist film by the developing solution, to create an evaluation

10 substrate; and  
11 splitting said evaluation substrate in a cross section perpendicular to the lengthwise  
12 direction of said line such that it is possible to observe said cross section.

1 12. (new) A method of evaluating a photoresist pattern according to claim 11, wherein when  
2 creating said evaluation substrate, a plurality of photoresist patterns with reinforcing sections are  
3 formed such that lengthwise directions of line sections are parallel, and locations of reinforcing  
4 sections in the lengthwise direction of the line sections are different for adjacent photoresist  
5 patterns with reinforcing sections.

1 13. (new) A method of manufacturing a device using a lithographic method that includes a  
2 process of forming on a substrate a photoresist pattern having a line section on at least part  
3 thereof, said method comprising:  
4 forming on a substrate a photoresist pattern with a reinforcing section, wherein there is  
5 provided a line section and a reinforcing section that continues to said line section and that has a  
6 greater width than a line width of said line section, or a plurality of such reinforcing sections  
7 with spaces between themselves;  
8 providing on the substrate a sublayer film that is soluble in a developing solution used in  
9 a developing process;  
10 forming on the sublayer film a photoresist film, exposing the photoresist film; and  
11 delveloping the photoresist film by the developing solution.